



DMN2055U

#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
201/	$38m\Omega$ @ $V_{GS} = 4.5V$	4.8A
20V	$45m\Omega @ V_{GS} = 2.5V$	4.5A

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- General Purpose Interfacing Switch
- Power Management Functions

### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

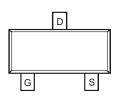
#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

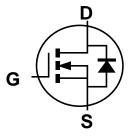
SOT23







Top View



**Equivalent Circuit** 

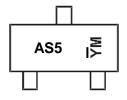
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2055U-7	SOT23	3,000/Tape & Reel
DMN2055U-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



Date Code Key

Year	2017	2018	20	019	2020	2021		2022	2023	202	24	2025
Code	Е	F		G	Н			J	K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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# **Maximum Ratings** $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage		V <sub>GSS</sub>	±8	V	
Continuous Drain Current (Note 6) Steady $T_A = +25^{\circ}\text{C}$ State $T_A = +85^{\circ}\text{C}$			I <sub>D</sub>	4.8 3.8	А
Pulsed Drain Current (10µs Pulse, Dut	y Cycle = 1%)		I <sub>DM</sub>	25	Α

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

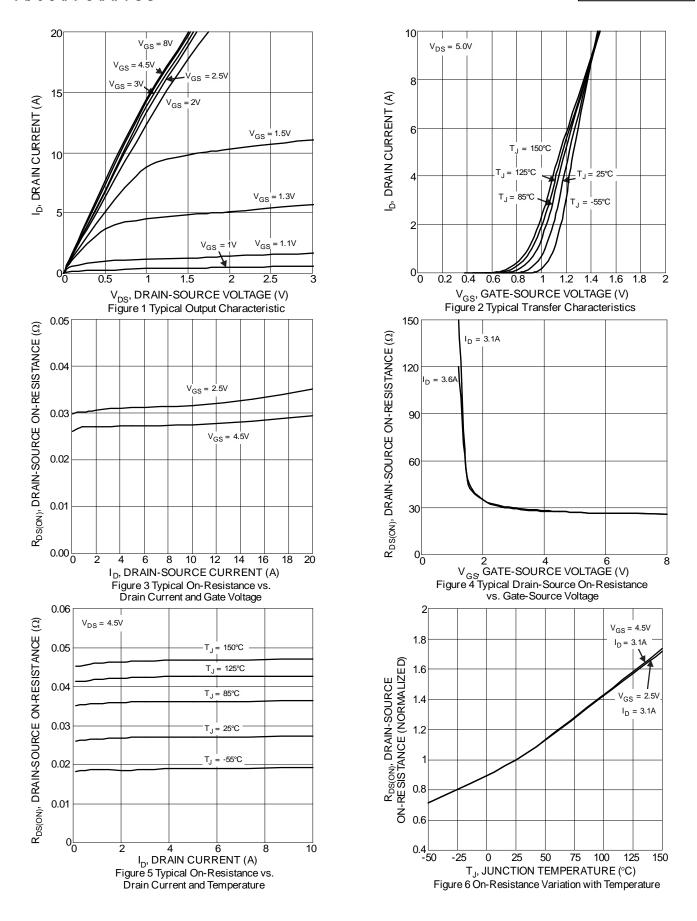
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		$P_D$	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	162	°C/W	
Total Power Dissipation (Note 6)	•	P <sub>D</sub>	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	113	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

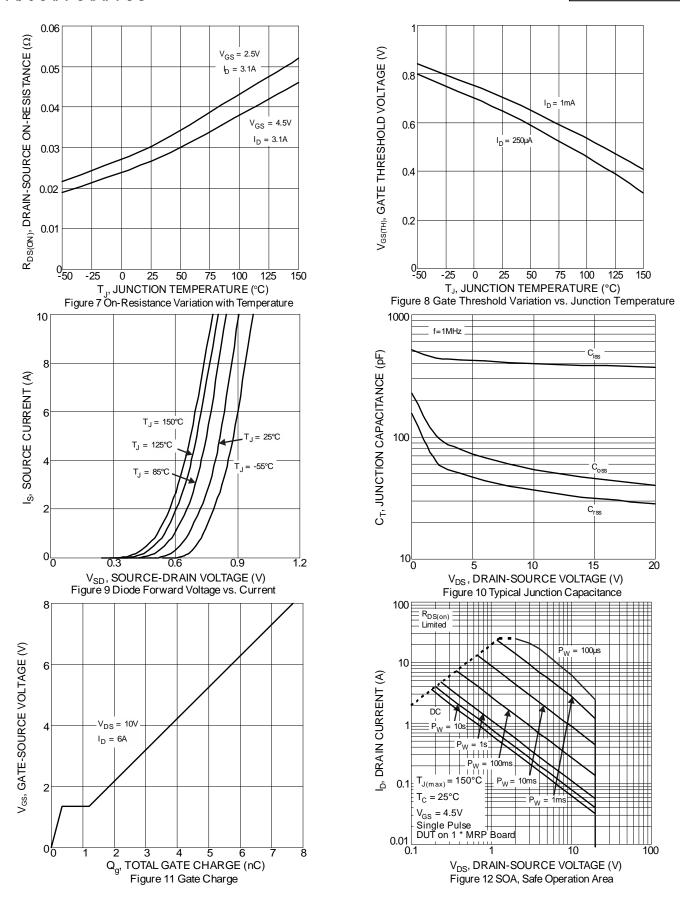
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1.0	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$		
Static Drain-Source On-Resistance	5		28	38	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$		
Static Dialif-Source Off-Resistance	R <sub>DS(ON)</sub>	_	32	45	11122	$V_{GS} = 2.5V, I_D = 3.1A$		
Diode Forward Voltage	$V_{SD}$	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$		
DYNAMIC CHARACTERISTICS (Note 8)	DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		400	_	pF			
Output Capacitance	Coss	_	55	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	37	_	pF	1 = 1.000112		
Gate Resistance	$R_{G}$	_	3.7	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$		
Total Gate Charge	$Q_{G}$	_	4.3	_	nC			
Gate-Source Charge	Q <sub>GS</sub>	_	0.3	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$		
Gate-Drain Charge	$Q_{GD}$	_	4.8	_	nC	$I_D = 6A$		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	2.8	_	ns			
Turn-On Rise Time	t <sub>R</sub>		2.7	_	ns	$V_{DD} = 10V, V_{GS} = 5V,$		
Turn-Off Delay Time	t <sub>D(OFF)</sub>		15.4	_	ns	$R_L = 1.7\Omega$ , $R_G = 6\Omega$		
Turn-Off Fall Time	t <sub>F</sub>		4.4	_	ns	1		
Reverse Recovery Time	t <sub>RR</sub>	1	6.8	-	ns	$I_F = 1.0A$ , $di/dt = 100A/\mu s$		
Reverse Recovery Charge	Q <sub>RR</sub>		1.2	_	nC	$I_F = 1.0A$ , $di/dt = 100A/\mu s$		

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:

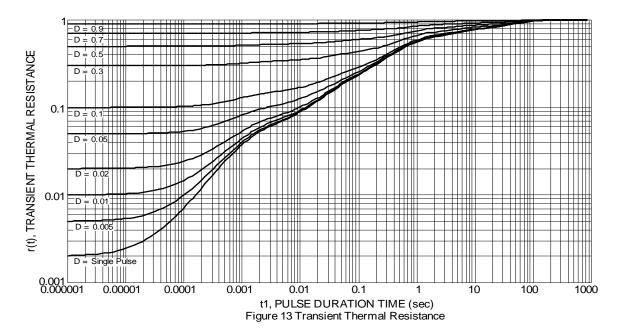










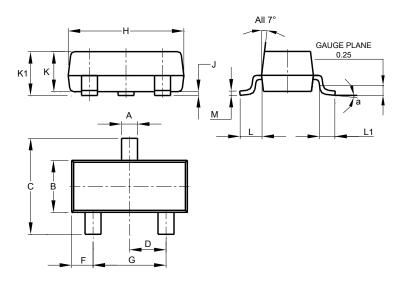




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

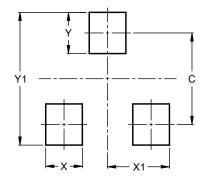


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
١	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Y	0.9				
V1	2.0				



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